

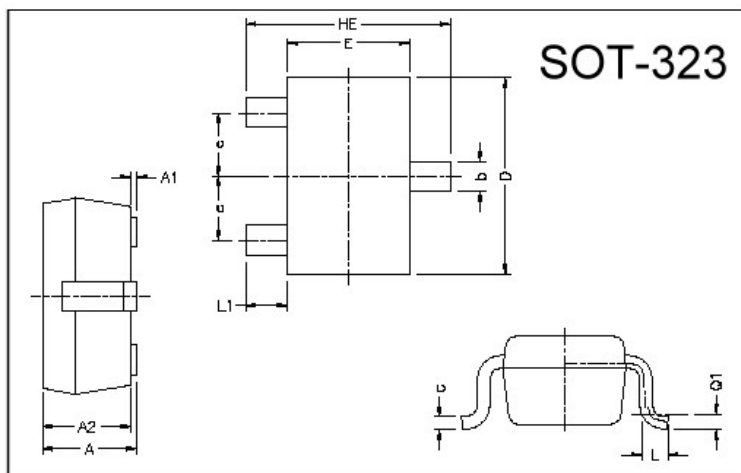
## GS401SD

**SURFACE MOUNT, SCHOTTKY BARRIER DIODE**  
**VOLTAGE 30V, CURRENT 0.2A**

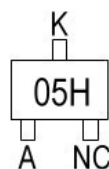
### Description

The GS401SD is high frequency rectification for switching power supply.

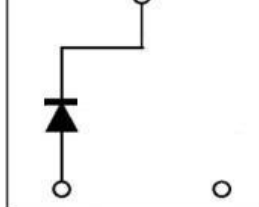
### Package Dimensions



Marking :



Circuit :



| REF. | Millimeter |      | REF. | Millimeter |      |
|------|------------|------|------|------------|------|
|      | Min.       | Max. |      | Min.       | Max. |
| A    | 0.80       | 1.10 | L1   | 0.42 REF.  |      |
| A1   | 0          | 0.10 | L    | 0.15       | 0.35 |
| A2   | 0.80       | 1.00 | b    | 0.25       | 0.40 |
| D    | 1.80       | 2.20 | c    | 0.10       | 0.25 |
| E    | 1.15       | 1.35 | e    | 0.65 REF.  |      |
| HE   | 1.80       | 2.40 | Q1   | 0.15 BSC.  |      |

### Absolute Maximum Ratings at TA = 25°C

| Parameter                                                   | Symbol           | Ratings    | Unit |
|-------------------------------------------------------------|------------------|------------|------|
| Junction Temperature                                        | Tj               | +125       | °C   |
| Storage Temperature                                         | Tstg             | -55 ~ +125 | °C   |
| Maximum Recurrent Peak Reverse Voltage                      | V <sub>RRM</sub> | 30         | V    |
| Maximum RMS Voltage                                         | V <sub>RMS</sub> | 21         | V    |
| Maximum DC Blocking Voltage                                 | V <sub>DC</sub>  | 30         | V    |
| Peak Forward Surge Current at 8.3mSec single half sine-wave | I <sub>FSM</sub> | 3.0        | A    |
| Typical Junction Capacitance between Terminal (Note 1)      | C <sub>J</sub>   | 40         | pF   |
| Maximum Average Forward Rectified Current                   | I <sub>o</sub>   | 0.2        | A    |
| Total Power Dissipation                                     | PD               | 225        | mW   |

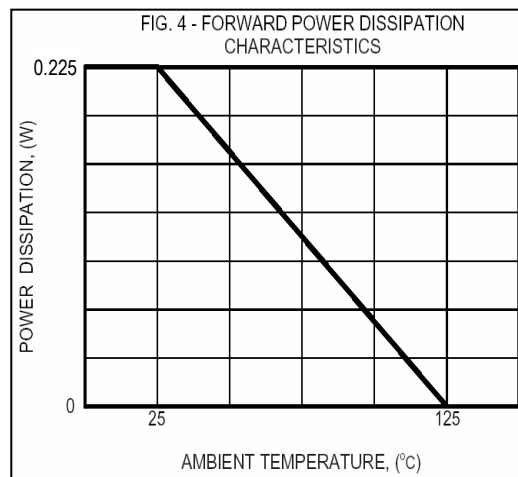
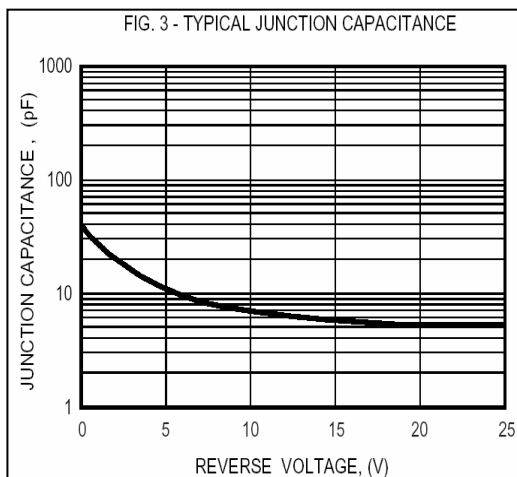
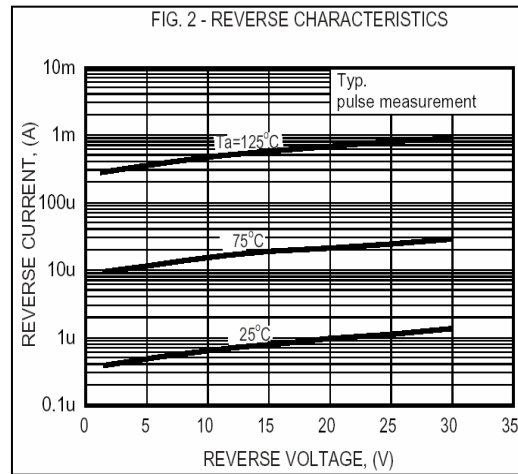
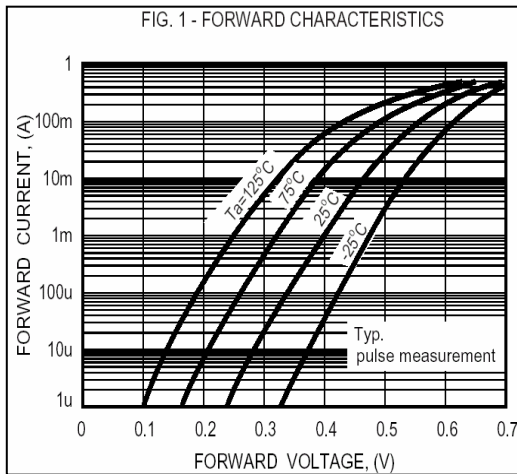
### Electrical Characteristics (at TA = 25°C unless otherwise noted)

| Parameter                             | Symbol             | Min. | Typ. | Max. | Unit | Test Conditions |
|---------------------------------------|--------------------|------|------|------|------|-----------------|
| Reverse Breakdown Voltage             | V <sub>(BR)R</sub> | 30   | -    | -    | V    | IR=100μA        |
| Maximum Instantaneous Forward Voltage | V <sub>F</sub>     | -    | -    | 500  | mV   | IF=200mA        |
| Maximum Average Reverse Current       | I <sub>R</sub>     | -    | -    | 50   | μA   | VR1=10V         |
|                                       |                    | -    | -    | 100  | μA   | VR2=30V         |

Notes: 1. Measured at 1.0 MHz and 0 reverse bias voltage.

2. ESD sensitive product handling required.

## Characteristics Curve



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